

PATENT APPLN. NO. 10/563,801
RESPONSE UNDER 37 C.F.R. §1.111

IN THE CLAIMS:

1 - 16. (canceled)

17. (currently amended) A poly(organo siloxane) compound formed via a CVD process and comprising a repeating Si-O backbone, carbon chain crosslinking groups and $-R^1-R^2$ bound to from 5 % to 60 % of the silicon atoms in the Si-O backbone, wherein R^2 is an aromatic group having 6 carbon atoms and R^1 is a substituent at position 4 of R^2 .

18 - 34. (canceled)

35. (currently amended) A poly(organo siloxane) compound formed via ~~[[the]]~~ a CVD method and comprising a repeating Si-O backbone, $-R^1-R^2$ bound to from 25 % to 60 % of the silicon atoms in the Si-O backbone, wherein R^2 is an aromatic group having 6 carbon atoms and R^1 is a substituent at position 4 of R^2 or a group directly linked to Si, and R^3 is bound to from 5 % to 60 % of the silicon atoms, wherein R^3 is an alkenyl group having from 2 to 5 carbon atoms, acrylic group or epoxy group.

36 - 50. (canceled)

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51. (currently amended) An integrated circuit having a layer with areas of an electrically conductive first material and an electrically insulating second material, wherein the second material is a poly(organo siloxane) compound deposited via a CVD method and comprising a repeating Si-O backbone, carbon chain crosslinking groups and $-R^1-R^2$ bound to from 5 % to 60 % of the silicon atoms in the Si-O backbone, wherein R^2 is an aromatic group having 6 carbon atoms and R^1 is a substituent at position 4 of R^2 .

52 - 61. (canceled)

62. (currently amended) A computer comprising an integrated circuit having a layer with areas of an electrically conductive first material and an electrically insulating second material, wherein the second material is a poly(organo siloxane) compound deposited via a CVD method and comprising a repeating Si-O backbone, carbon chain crosslinking groups and $-R1-R2$ bound to from 5 % to 60 % of the silicon atoms in the Si-O backbone, wherein $R2$ is an aromatic group having 6 carbon atoms and $R1$ is a substituent at position 4 of $R2$.

63. (currently amended) A method for making an integrated circuit, comprising providing alternating areas of electrically

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insulating and electrically conducting materials within a layer on a semiconductor substrate, wherein the electrically insulating material comprises a poly(organo siloxane) compound deposited via a CVD method and comprising a repeating Si-O backbone, carbon chain crosslinking groups and -R1-R2 bound to from 5 % to 60 % of the silicon atoms in the Si-O backbone, wherein R2 is an aromatic group having 6 carbon atoms and R1 is a substituent at position 4 of R2 selected from an alkyl chain having from 1 to 4 carbons, an alkenyl group having from 2 to 6 carbons or OH.

64 - 66. (canceled)